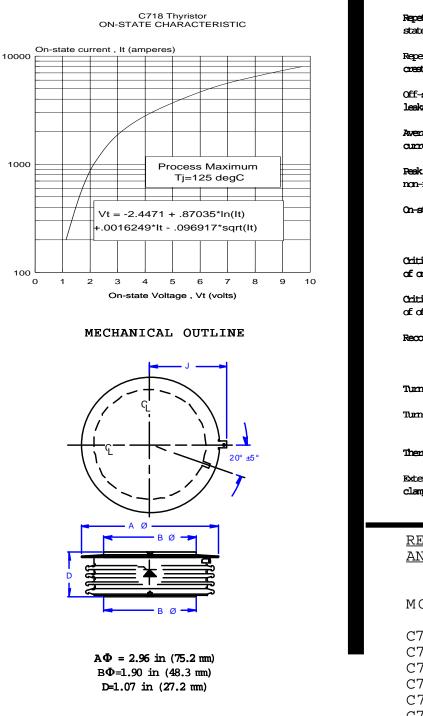


C718

53mm / 5.0 kV THYRISTOR

Type C718 thyristor is suitable for phase control applications such as HMDC valves, static VAR compensators and synchronous motor drives.

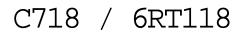
The silicon junction is manufactured by the proven multi-diffusion process and is supplied in an industry standard disc-type package, ready to mount to forced or naturally cooled heat dissipators using connercially available mechanical clamping hardware.



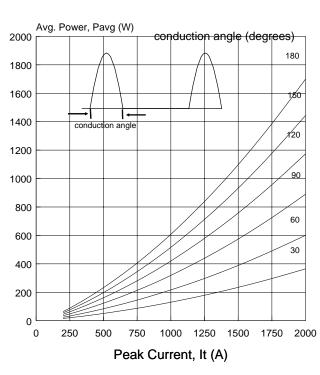
PRINCIPAL RATINGS AND CHARACTERISTICS

Repetitive peak off- state & revense volts	V _{drm} V _{rrm}	T ₃ =0 to 125℃	up to 5000	v
Repetitive working creat voltage	V _{dwm} V _{drm}	T _J =0 to 125℃	0.8V _{drm} 0.8V _{rrm}	
Off-state & revense leakage current	Ъ _{им} І _{ким}	T _J =0 to 125℃	75 75	ma
Average on-state cument	Ţ _{t(av)}	T‱= 70℃	750	A
Peak half-cycle non-rep surge current	I _{tsm}	60 Hz 50 Hz	7 6.5	kA
On-state voltage	V _{т м}	I _r =1kA t _p =8ms T _g =125℃	2.1	v
Oritical rate of rise of constate current	di/dt. 115p	T _J =125℃ 60 Hz	75	A/us
Oritical rate of rise of off-state voltage	dv/dt	т _ј =125℃ V _D =.67V _{DRM}	1000	V/us
Recovery current	Т км	T _, =125℃ 24∕us 54⁄us	60 100	A
Turn-on delay	ťa	Vd=.5V _{DRM}	3	ນຮ
Turn-off time	T _œ	5A/us,-100V 20V/us to 2000V	500	US
Thermal resistance	R _{thjc}		.025	c/w
Externally applied clamping force	F		5500 24.5	h s. kN

REPETITI	•	REVERSE				
<u>and off-</u>	<u>STATE</u> E	<u>BLOCKING</u>				
VOLTAGE						
T _. = 0 to 125°C						
MODEĽ	V _{drm}	$V_{_{RRM}}$				
	(volts)	(valts)				
C718EP	5000	5000				
C718DT	4900	4900				
C718DN	4800	4800				
C718DS	4700	4700				
C718DM	4600	4600				
C718DE	4500	4500				

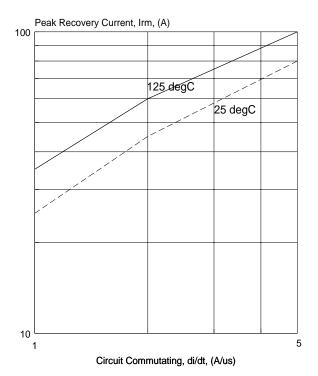




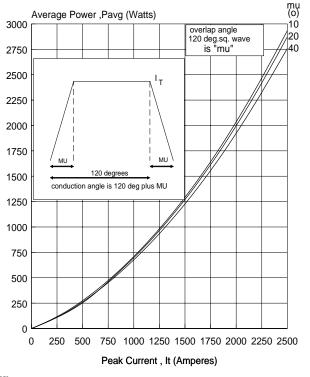


Full Cycle Average Power Loss per C718 Thyristor

MAXIMUM PEAK RECOVERY CURRENT versus COMMUTATING di/dt



FULL CYCLE AVERAGE POWER LOSS versus PEAK CURRENT at 50/60 Hz (plasma spreading and conduction loss)



GATE SUPPLY REQUIREMENTS

3 A 0.5.5

Pulse duration (min) 20 us